

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74HC595AP, TC74HC595AF, TC74HC595AFN

## 8-BIT SHIFT REGISTER / LATCH (3-STATE)

(Note) The JEDEC SOP (FN) is not available in Japan.

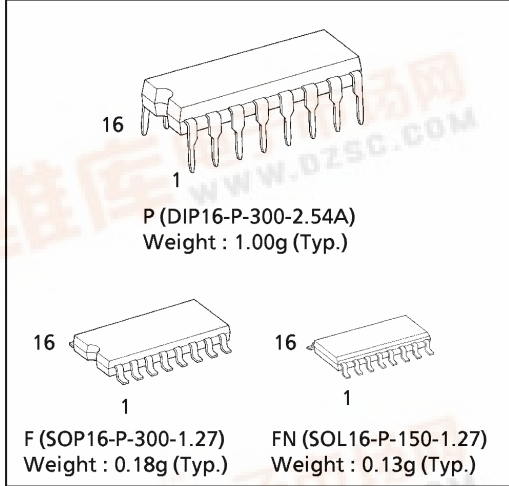
The TC74HC595A is a high speed 8-BIT SHIFT REGISTER / LATCH fabricated with silicon gate C<sup>2</sup>MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. The TC74HC595A contains an 8-bit static shift register which feeds an 8-bit storage register.

Shift operation is accomplished on the positive going transition of the SCK input. The output register is loaded with the contents of the shift register on the positive going transition of the RCK input. Since RCK and SCK signal are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3-state, it can be directly connected to 8-bit bus. This register can be used in serial-to-parallel conversion, data receivers, etc.

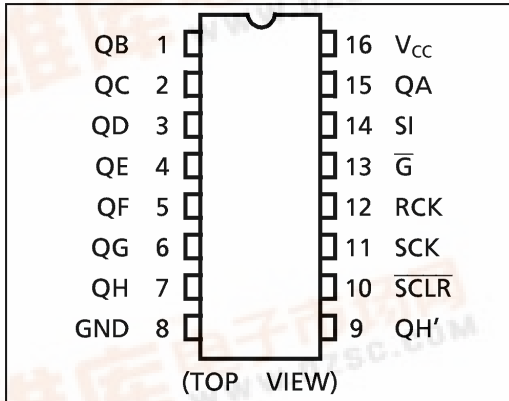
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### FEATURES :

- High Speed..... $f_{MAX} = 55\text{MHz}(\text{typ.})$   
at  $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$  at  $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC} (\text{Min.})$
- Output Drive Capability..... 15 LSTTL Loads For QA~QH  
10 LSTTL Loads For QH'
- Symmetrical Output Impedance...  $|I_{OH}| = I_{OL} = 6\text{mA}(\text{Min.})$   
For QA~QH  
 $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$   
For QH'
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range...  $V_{CC} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS595



### PIN ASSIGNMENT



### TRUTH TABLE

INPUTS					FUNCTION
SI	SCK	SCLR	RCK	G-bar	
X	X	X	X	H	QA thru QH outputs disable
X	X	X	X	L	QA thru QH outputs enable
X	X	L	X	X	Shift register is cleared.
L		H	X	X	First stage of S. R. becomes "L". Other stages store the data of previous stage, respectively.
H		H	X	X	First stage of S. R. becomes "H". Other stages store the data of previous stage, respectively.
X		H	X	X	State of S. R. is not changed.
X	X	X		X	S.R. data is stored into storage register.
X	X	X		X	Storage register stage is not changed.

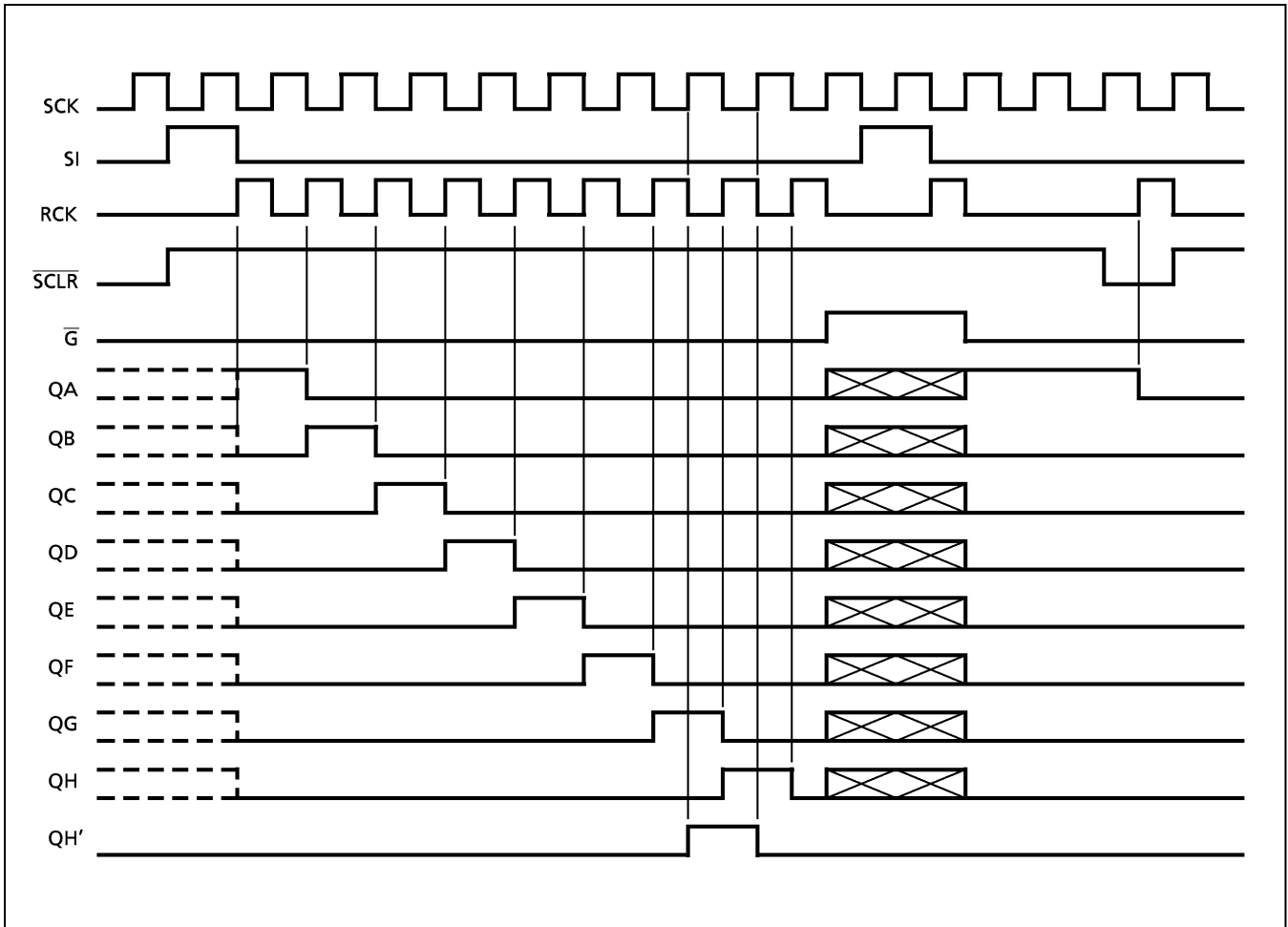
X : Don't Care

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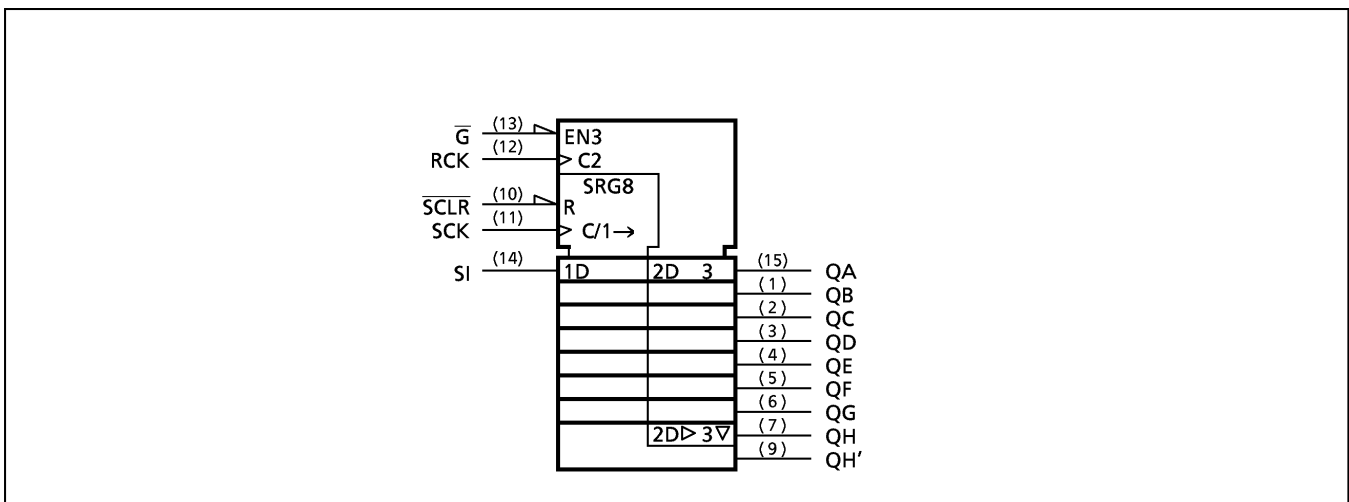
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**TIMING CHART**



**IEC LOGIC SYMBOL**



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## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7	V
DC Input Voltage	$V_{IN}$	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	±20	mA
Output Diode Current	$I_{OK}$	±20	mA
DC Output Current (QH') (QA~QH)	$I_{OUT}$	±25 ±35	mA
DC $V_{CC}$ / Ground Current	$I_{CC}$	±75	mA
Power Dissipation	$P_D$	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	$T_{stg}$	-65~150	°C

\*500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ . From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  shall be applied until 300mW.

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	2~6	V
Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$t_r, t_f$	0~1000 ( $V_{CC} = 2.0\text{V}$ ) 0~500 ( $V_{CC} = 4.5\text{V}$ ) 0~400 ( $V_{CC} = 6.0\text{V}$ )	ns

## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	$V_{IH}$		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V	
Low - Level Input Voltage	$V_{IL}$		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V	
High - Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —	V
		QH'	$I_{OH} = -4\text{ mA}$ $I_{OH} = -5.2\text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	— —	
		QA~QH	$I_{OH} = -6\text{ mA}$ $I_{OH} = -7.8\text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	— —	
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
		QH'	$I_{OL} = 4\text{ mA}$ $I_{OL} = 5.2\text{ mA}$	4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33	
		QA~QH	$I_{OL} = 6\text{ mA}$ $I_{OL} = 7.8\text{ mA}$	4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33	
3 - State Output Off - State Current	$I_{OZ}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$ or GND	6.0	—	—	±0.5	—	±5.0	$\mu\text{A}$	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	±0.1	—	±1.0		
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0		

TIMING REQUIREMENTS ( Input  $t_r = t_f = 6\text{ns}$  )

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	Ta = 25°C		Ta = -40~85°C	UNIT
				TYP.	LIMIT	LIMIT	
Minimum Pulse Width (SCK, RCK )	$t_{W(H)}$ $t_{W(L)}$		2.0	—	75	95	ns
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Pulse Width ( $\overline{\text{SCLR}}$ )	$t_{W(L)}$		2.0	—	75	95	
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Set-up Time (SI—SCK)	$t_s$		2.0	—	50	65	
			4.5	—	10	13	
			6.0	—	9	11	
Minimum Set-up Time (SCK—RCK)	$t_s$		2.0	—	75	95	
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Set-up Time ( $\overline{\text{SCLR}}$ —RCK)	$t_s$		2.0	—	100	125	
			4.5	—	20	25	
			6.0	—	17	21	
Minimum Hold Time	$t_h$		2.0	—	0	0	
			4.5	—	0	0	
			6.0	—	0	0	
Minimum Removal Time ( $\overline{\text{SCLR}}$ )	$t_{rem}$		2.0	—	50	65	
			4.5	—	10	13	
			6.0	—	9	11	
Clock Frequency	f		2.0	—	6	5	MHz
			4.5	—	30	25	
			6.0	—	35	28	

**AC ELECTRICAL CHARACTERISTICS (  $C_L = 15\text{pF}$ ,  $V_{CC} = 5\text{V}$ ,  $T_a = 25^\circ\text{C}$ , Input  $t_r = t_f = 6\text{ns}$  )**

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time (QH')	$t_{TLH}$ $t_{THL}$		—	4	8	ns
Propagation Delay Time (SCK—QH')	$t_{pLH}$ $t_{pHL}$		—	12	21	
Propagation Delay Time (SCLR—QH')	$t_{pHL}$		—	15	30	
Maximum Clock Frequency	$f_{MAX}$		35	77	—	MHz

**AC ELECTRICAL CHARACTERISTICS ( Input  $t_r = t_f = 6\text{ns}$  )**

PARAMETER	SYMBOL	TEST CONDITION	CL (pF)	V <sub>CC</sub> (V)	T <sub>a</sub> = 25°C			T <sub>a</sub> = -40~85°C		UNIT
					MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time (Q <sub>n</sub> )	$t_{TLH}$ $t_{THL}$		50	2.0	—	25	60	—	75	ns
				4.5	—	7	12	—	15	
				6.0	—	6	10	—	13	
Output Transition Time (QH')	$t_{TLH}$ $t_{THL}$		50	2.0	—	30	75	—	95	
				4.5	—	8	15	—	19	
				6.0	—	7	13	—	16	
Propagation Delay Time (SCK—QH')	$t_{pLH}$ $t_{pHL}$		50	2.0	—	45	125	—	155	
				4.5	—	15	25	—	31	
				6.0	—	13	21	—	26	
Propagation Delay Time (SCLR—QH')	$t_{pHL}$		50	2.0	—	60	175	—	220	
				4.5	—	18	35	—	44	
				6.0	—	15	30	—	37	
Propagation Delay Time (RCK—Q <sub>n</sub> )	$t_{pLH}$ $t_{pHL}$		50	2.0	—	60	150	—	190	
				4.5	—	20	30	—	38	
				6.0	—	17	26	—	32	
			150	2.0	—	75	190	—	240	
				4.5	—	25	38	—	48	
				6.0	—	22	32	—	41	
Output Enable time	$t_{pZL}$ $t_{pZH}$	R <sub>L</sub> = 1kΩ	50	2.0	—	45	135	—	170	
				4.5	—	15	27	—	34	
				6.0	—	13	23	—	29	
			150	2.0	—	60	175	—	220	
				4.5	—	20	35	—	44	
				6.0	—	17	30	—	37	
Output Disable time	$t_{pLZ}$ $t_{pHZ}$	R <sub>L</sub> = 1kΩ	50	2.0	—	30	150	—	190	
				4.5	—	15	30	—	38	
				6.0	—	14	26	—	33	
Maximum Clock Frequency	$f_{MAX}$		50	2.0	6	17	—	5	—	
				4.5	30	50	—	25	—	
				6.0	35	59	—	28	—	
Input Capacitance	C <sub>IN</sub>				—	5	10	—	10	pF
Power Dissipation Capacitance	C <sub>PD(1)</sub>				—	184	—	—	—	

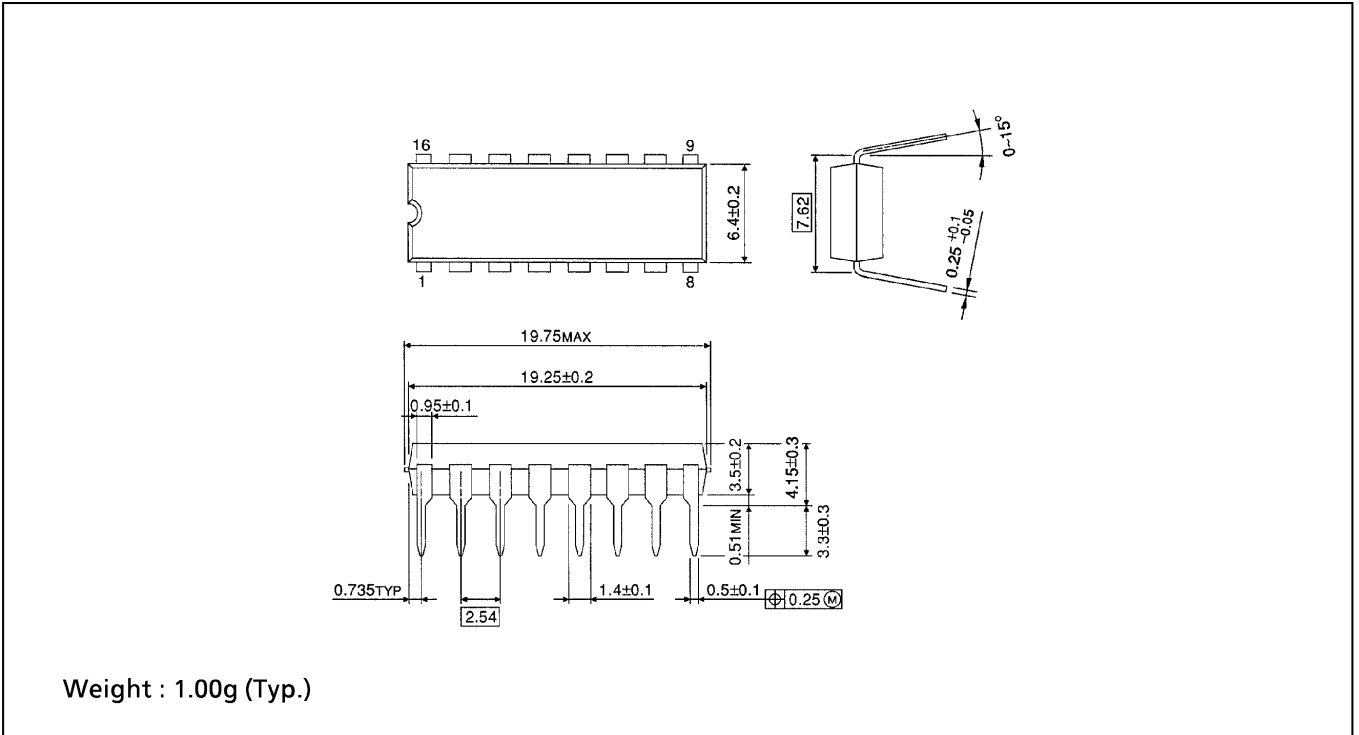
Note(1): C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

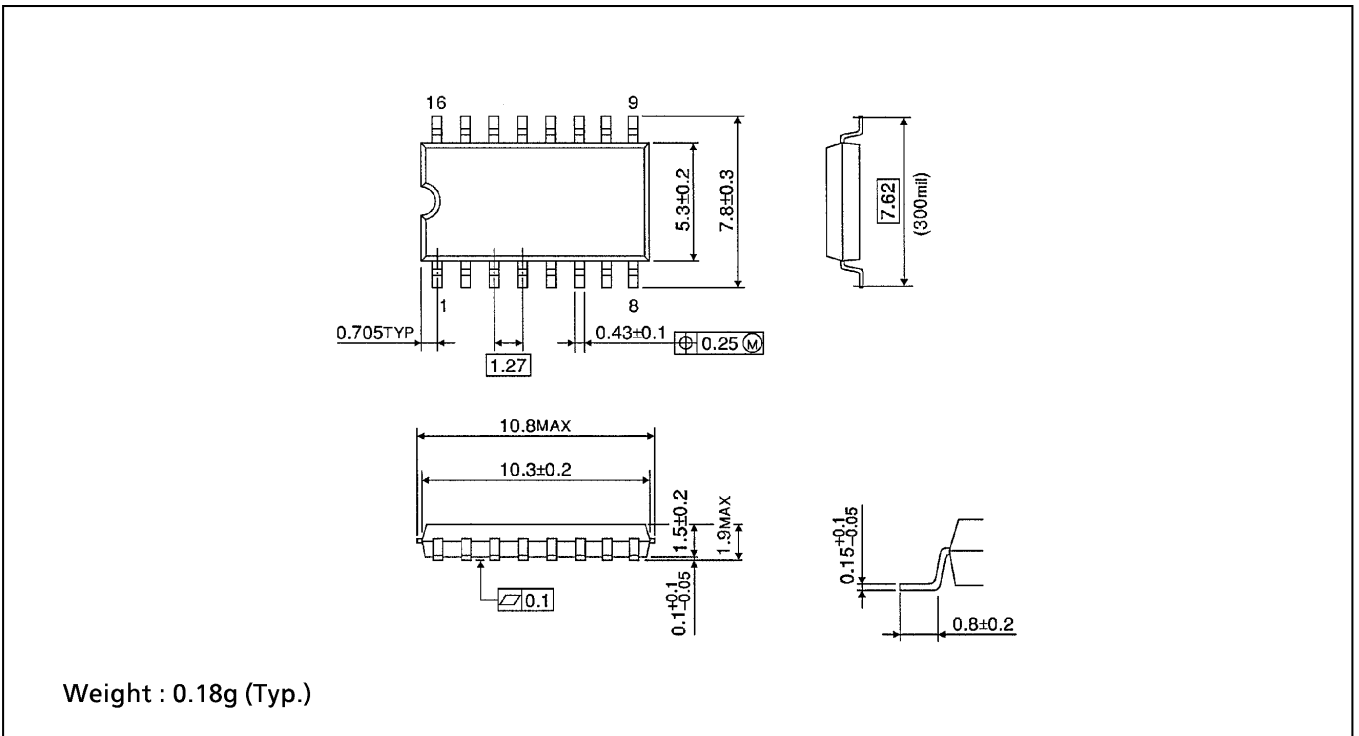
**DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)**

Unit in mm



**SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)**

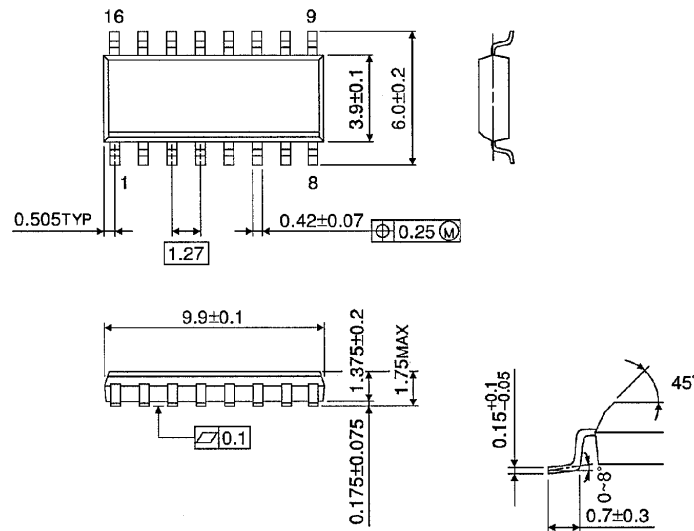
Unit in mm



**SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150 -1.27)**

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)